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DERWENT-ACC-NO:         2002-188205

DERWENT-WEEK:           200355

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TITLE:                  Abrasion material for use for polishing
semiconductors
                       comprises a polishing part obtained by molding
a powder
                       obtained by removing the dispersant from a
dispersion of
                       a matrix and cerium oxide powder

INVENTOR: HASEGAWA, K; HOSAKA, Y ; ISHIKAWA, O ; SATOU, H

PATENT-ASSIGNEE:  JSR CORP[JAPS] ,  HASEGAWA K[HASEI],  HOSAKA
Y[HOSAI],
     ISHIKAWA O[ISHII],  SATOU H[SATOI]

PRIORITY-DATA: 2000JP-0161519 (May 31, 2000)

PATENT-FAMILY:
PUB-NO                    PUB-DATE                   LANGUAGE
PAGES      MAIN-IPC
US 20030153255 A1         August 14, 2003            N/A
000        B24D 011/00
WO 200191975 A1           December 6, 2001           J
030        B24D 003/20
KR 2002019595 A           March 12, 2002             N/A
000        B24D 003/00
EP 1295682 A1             March 26, 2003             E
000        B24D 003/20
JP 2001587972 X           August 5, 2003             N/A
000        B24D 003/28


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APPL-DATE
US20030153255A1      N/A                       2001WO-JP04483
May 29, 2001
US20030153255A1      N/A                       2002US-0030141
November 15, 2002
WO 200191975A1       N/A                       2001WO-JP04483
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			May 29, 2001
KR2002019595A	N/A	2002KR-0701332	January 30, 2002
EP 1295682A1	N/A	2001EP-0934382	May 29, 2001
EP 1295682A1	N/A	2001WO-JP04483	May 29, 2001
EP 1295682A1	Based on	WO 200191975	N/A
JP2001587972X	N/A	2001JP-0587972	May 29, 2001
JP2001587972X	N/A	2001WO-JP04483	May 29, 2001
JP2001587972X	Based on	WO 200191975	N/A

INT-CL (IPC): B24D003/00, B24D003/20 , B24D003/28 , B24D003/34 , B24D011/00

ABSTRACTED-PUB-NO: WO 200191975A

BASIC-ABSTRACT:

NOVELTY - An abrasion material comprises a polishing part produced by molding a mixture powder obtained by removing the dispersant from an aqueous dispersion of a matrix materials and cerium oxide powder.

DETAILED DESCRIPTION - The mixture material is obtained by reacting butadiene, styrene, methyl methacrylate, itaconic acid, acrylic acid, alpha --methylstyrene dimer, and t-dodecyl mercaptan at 75 deg. C in an autoclave for 16 hours, adjusting the pH of the resultant emulsion to 8.5, adding cerium oxide powder (particulate diameter = 0.3 mu m), stirring the mixture so as to obtain an aqueous dispersion, thinly spreading the aqueous dispersion on a film, drying and press-molding.

USE - The abrasion material is for use for polishing semiconductors.

ADVANTAGE - The abrasion material has excellent and stable properties and is effective in reducing the number of scratches.

CHOSEN-DRAWING: Dwg.0/0

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TITLE-TERMS: ABRASION MATERIAL POLISH SEMICONDUCTOR COMPRISE POLISH
PART OBTAIN
             MOULD POWDER OBTAIN REMOVE DISPERSE DISPERSE MATRIX
CERIUM OXIDE
             POWDER

DERWENT-CLASS:  A88 P61

CPI-CODES:  A04-B03; A04-B05; A04-C05; A04-F01A; A08-R; A11-B11; A12-
E07C;

ENHANCED-POLYMER-INDEXING:
Polymer Index [1.1]
    018 ; R00806 G0828 G0817 D01 D02 D12 D10 D51 D54 D56 D58 D84 ;
R00708
    G0102 G0022 D01 D02 D12 D10 D19 D18 D31 D51 D53 D58 D76 D88 ;
R00479
    G0384 G0339 G0260 G0022 D01 D11 D10 D12 D26 D51 D53 D58 D63 D85
    F41 F89 ; R00446 G0282 G0271 G0260 G0022 D01 D12 D10 D26 D51 D53
    D58 D60 D83 F36 F35 ; R00654 G0760 G0022 D01 D12 D10 D51 D53 D58
    D60 D85 F37 F35 E00 E03 ; R00673 G0102 G0022 D01 D02 D12 D10 D19
    D18 D31 D51 D53 D58 D76 D89 ; H0033 H0011 ; L9999 L2528 L2506 ;
    S9999 S1025 S1014 ; S9999 S1285*R ; S9999 S1434 ; L9999 L2391 ;
    L9999 L2073 ; M9999 M2073 ; P0328  ; P1741  ; P0088  ; P0146
Polymer Index [1.2]
    018 ; ND01 ; Q9999 Q6600 ; Q9999 Q7476 Q7330 ; K9416 ; N9999
N7147
    N7034 N7023 ; K9574 K9483
Polymer Index [1.3]
    018 ; N9999 N6440*R ; N9999 N6462 N6440 ; N9999 N6600 ; Q9999
Q7114*R
    ; N9999 N6780*R N6655 ; B9999 B5243*R B4740 ; B9999 B5287 B5276
    ; B9999 B4568*R
Polymer Index [2.1]
    018 ; R00326 G0044 G0033 G0022 D01 D02 D12 D10 D51 D53 D58 D82 ;
    H0000 ; S9999 S1285*R ; P1150  ; P1161
Polymer Index [2.2]
    018 ; ND01 ; Q9999 Q6600 ; Q9999 Q7476 Q7330 ; K9416 ; N9999
N7147
    N7034 N7023 ; K9574 K9483
Polymer Index [2.3]
    018 ; N9999 N7090 N7034 N7023 ; B9999 B5447 B5414 B5403 B5276


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